

**Amendments to the Specification**

Please replace paragraph [0025] and [0026] by the following amended paragraphs:

[0025] "The surface roughness (grain size) of the polysilicon layer formed by laser annealing is first increased by increasing the laser energy density, and then the surface roughness is reduced by increasing the laser energy density after the polysilicon layer is formed with the largest grain size. The inventor discovers that the light intensity of the light beam reflected from the polysilicon layer is increased ~~reduced~~ by increasing the grain size (surface roughness) of the polysilicon layer. Also, the light intensity is reduced ~~increased~~ by reducing the grain size after the polysilicon layer is formed with the largest grain size. Accordingly, the crystal quality of the polysilicon film can be monitored by the light intensity ratio. However, it is difficult to precisely detect the light intensity due to decay or interference in the probe light beam. Therefore, the invention utilizes the light intensity ratio as an index for inspecting crystal quality of the polysilicon film, thereby effectively eliminating the problem".

[0026] "FIG. 2 is a schematic of an apparatus for inspecting crystal quality of a polysilicon film according to the invention. In FIG. 2, a probe light beam L, such as a laser beam, is provided by a light source generator 200 to irradiate a polysilicon layer 102 ~~202~~ on a substrate 100, such as a glass substrate. A beam splitter 202 receives the probe light beam L to separate into a first light beam L1 and a second light beam L2. In the invention, the probe light beam L has a predetermined wavelength of about 266.about.316 nm. Moreover, the split ratio of the first light beam L1 to the second light beam L2 is about 30~40%:70~60%".